

Spin-on-Glass As-200

Elements of Interest Si, O, As	Key Element atoms/cm³ As, 4E+21	Key Element % in Film Arsenic
Viscosity, n (635nm) 1.1 cps, 1.49	Thickness Coats 250 nm at 3000 rpm	Shelf Life 20°C 3 months 4°C 9 months

Benefits

- Medium Arsenic doping level
- Uniform Coatings
- High purity materials
- Lower melting point than silica alone
- Stable processing independent of flow rates
- Available with impurity specification of less than 1 ppm or less than 50 ppb

Typical Application

This is a standard silicate arsenic doped glass very typical for semiconductor applications. It begins curing at about 200°C to give a less dense but solid film. It continues to become increasingly stronger as bakes continue to 650°C or higher. We recommend baking at the highest temperature the material will see in any post processing. For doping applications the glass is often removed after drive in.

The arsenic in the glass matrix can act as a diffusion barrier to prevent outgassing of doping material from the substrate.

Packaging

- 240ml
- 500ml
- 1 l
- 2.5 l
- 4 l

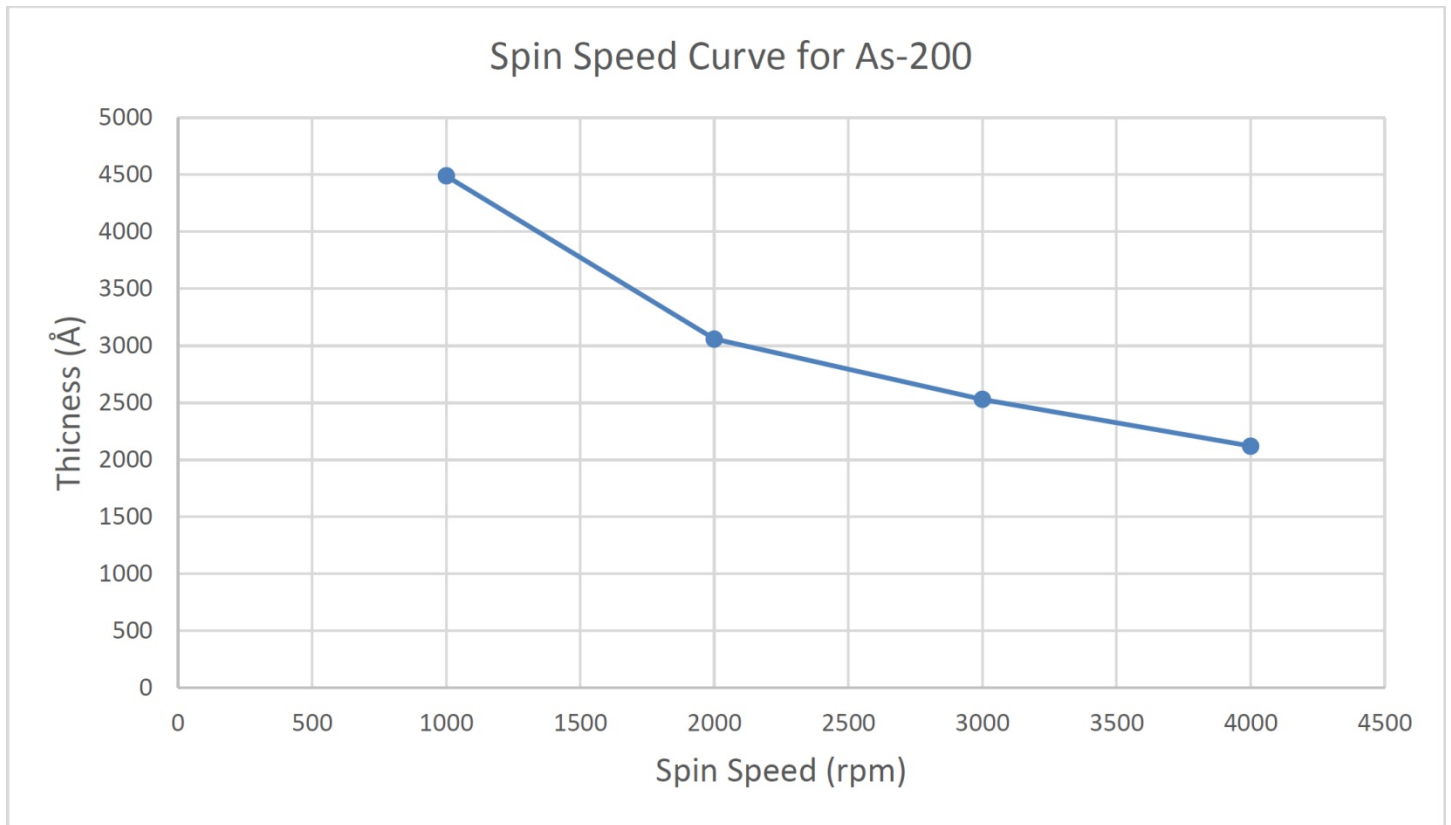
Alternative Products

As-300

Elements Available to Add

- Sb
- Bi
- Blends of two or more elements
- Other elements available for compound semiconductor use

Spin-on-Glass As-200



Although all statements and information presented in this document are believed to be accurate and reliable, they are presented without warranty or guarantee of any kind, express or implied. Information presented does not relieve the end user from carrying out their own tests to determine suitability for use in their application. User assumes all risk and liability for product use or information and results obtained. Suggestions for use of material and processes are made without representation or warranty that any such is free from patent infringement and are not recommendations for patent infringement. Please see MSDS for information regarding health and safety of material use.